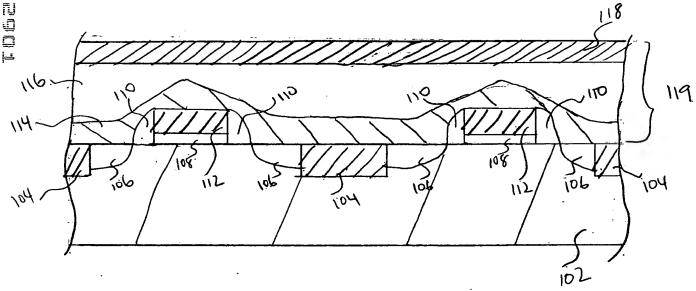


F16. 1A



F16. 1B

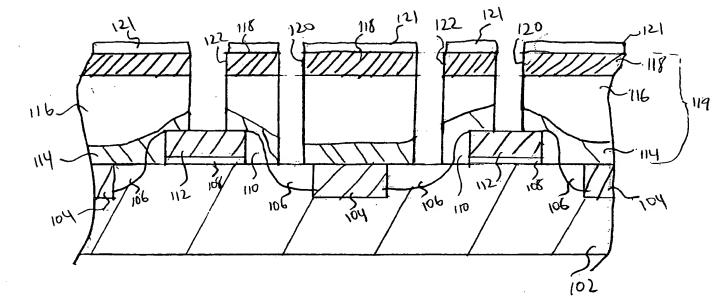
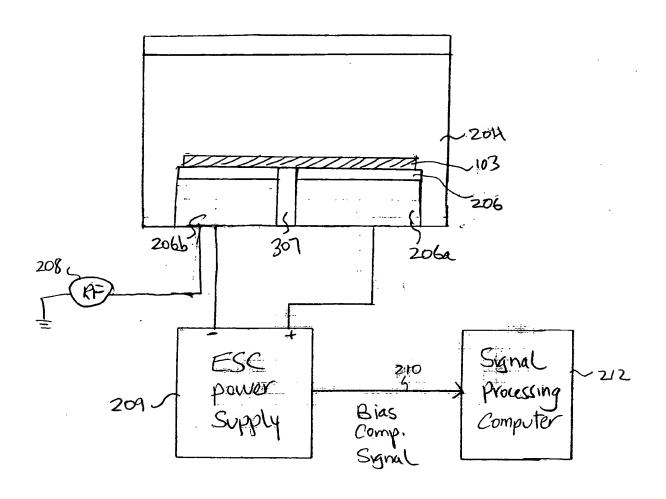
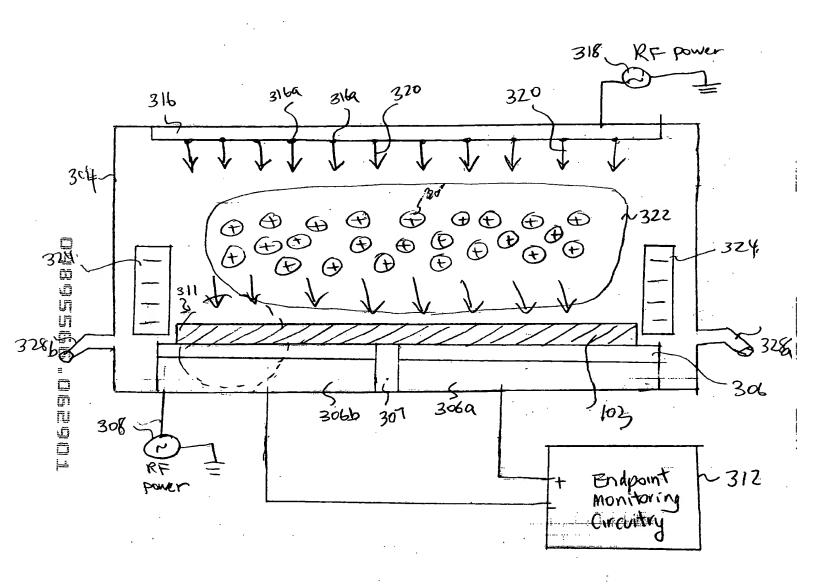


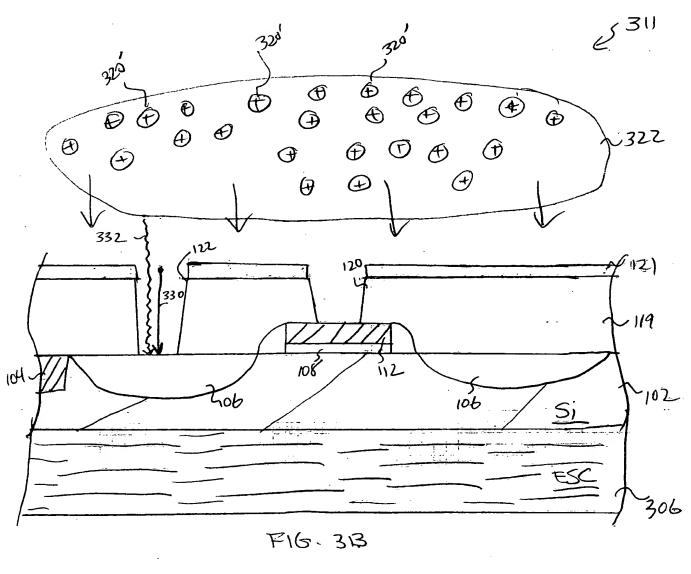
FIG 1C

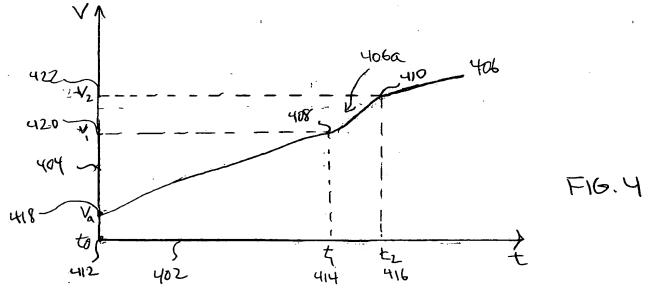


F16. 2



F16.3A

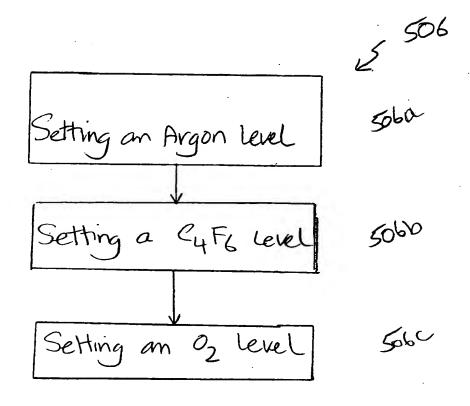




£ 500 Start Provide a Subtrate having 502 an ILD layer to be etched Inserting substrate into 504 a chamber In troducing etchant gases 50 6 Powering up the Chamber to strike a plasma to 508 commence etching Monitoring a substrate 50 bias level Discontinue the etching 512 when a target bias compansation Level is reached Removing substrate from chamber and prepare for additional processing it 514 disired

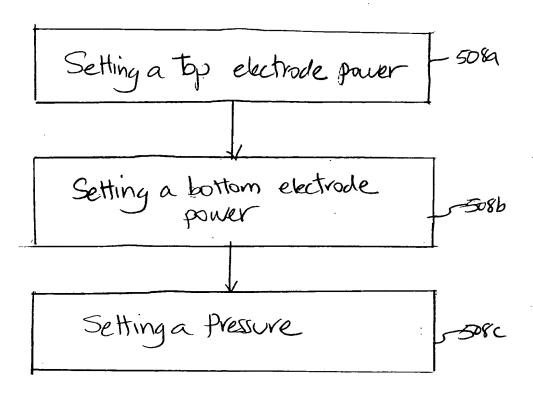
Done

F16.5A



F16.513





F16.5C